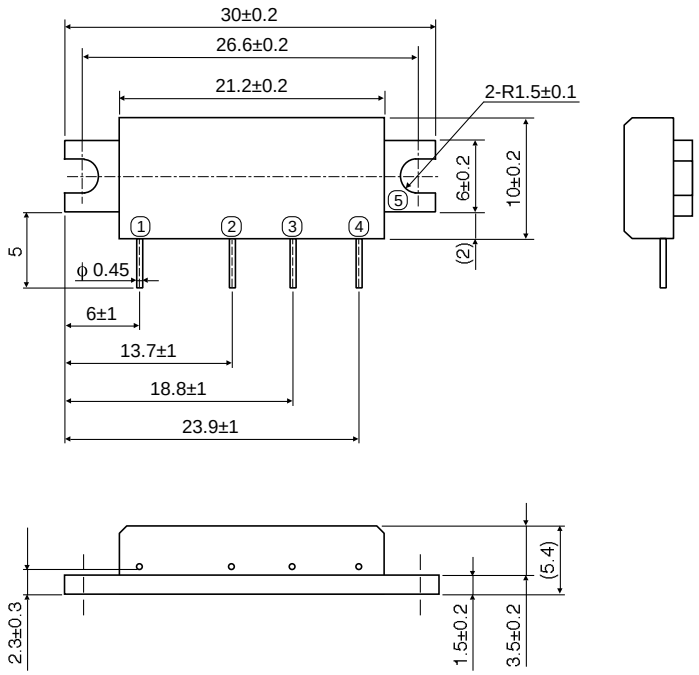
M68710TL

SILICON MOS FET POWER AMPLIFIER, 330-360MHz, 2W, FM PORTABLE RADIO

OUTLINE DRAWING

Dimensions in mm



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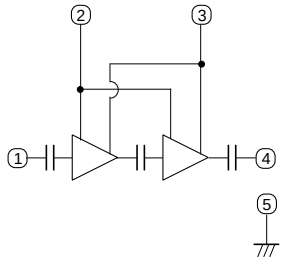
BLOCK DIAGRAM



PIN:
①P_{in} : RF INPUT
②V_{GG} : GATE BIAS SUPPLY
③V_{DD} : DRAIN BIAS SUPPLY
④P_O : RF OUTPUT
⑤GND: FIN

ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DD}	Supply voltage	V_{GG}≤3.5V, Z_G=Z_L=50Ω	9	V
V_{GG}	Gate bias voltage		4	V
P_{in}	Input power	f=330-360MHz, Z_G=Z_L=50Ω	30	mW
P_O	Output power	f=330-360MHz, V_{DD}≤9V, Z_G=Z_L=50Ω	3	W
$T_{C (OP)}$	Operation case temperature	f=330-360MHz, V_{DD}≤9V, Z_G=Z_L=50Ω	-30 to +110	°C
T_{stg}	Storage temperature		-40 to +110	°C

Note. Above parameters are guaranteed independently.

ELECTRICAL CHARACTERISTICS (Tc=25°C, Z_G=Z_L=50Ω unless otherwise noted)

Symbol	Parameter	Test conditions	Limits		Unit
			Min	Max	
f	Frequency range		330	360	MHz
P_O	Output power	V_{DD}=6V, V_{GG}=3.5V, P_{in}=20mW	2		W
η_T	Total efficiency		40		%
2f_O	2nd. harmonic			-25	dBc
ρ_{in}	Input VSWR			4	-
-	Stability	Z_G=50Ω, V_{DD}=4-8V, Load VSWR<4:1	No parasitic oscillation		-
-	Load VSWR tolerance	V_{DD}=9V, P_{in}=20mW, P_O=2W (V_{GG} adjust), Z_L=20:1	No degradation or destroy		-

Note. Above parameters, ratings, limits and test conditions are subject to change.